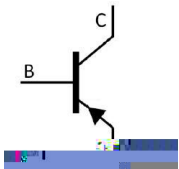


WR0<50 P ММ Ё SQS æ Ñ ç s ll 1 Silicon PNP transistor in a TO-92LM Plastic Package.

лъ 5VG99 : +D, Ы ´
Complementary pair with 2SD667(A).

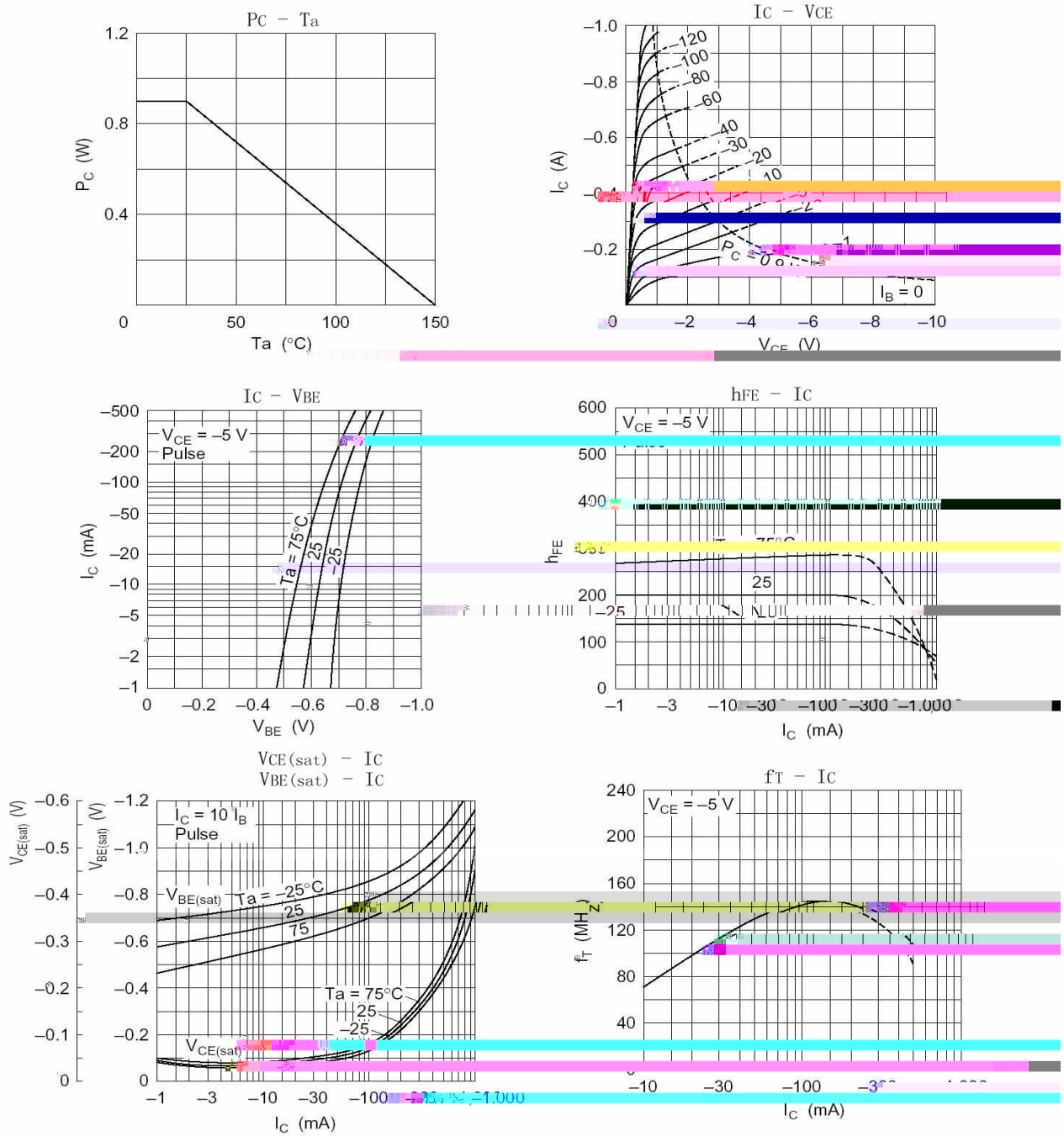
æ ç ã H l i ' ð z
Low frequency power amplifier.



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	2SB647 -80	V
		2SB647A -100	
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-1.0	A
Collector Current(Pulse)	I_{CP}	-2.0	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		

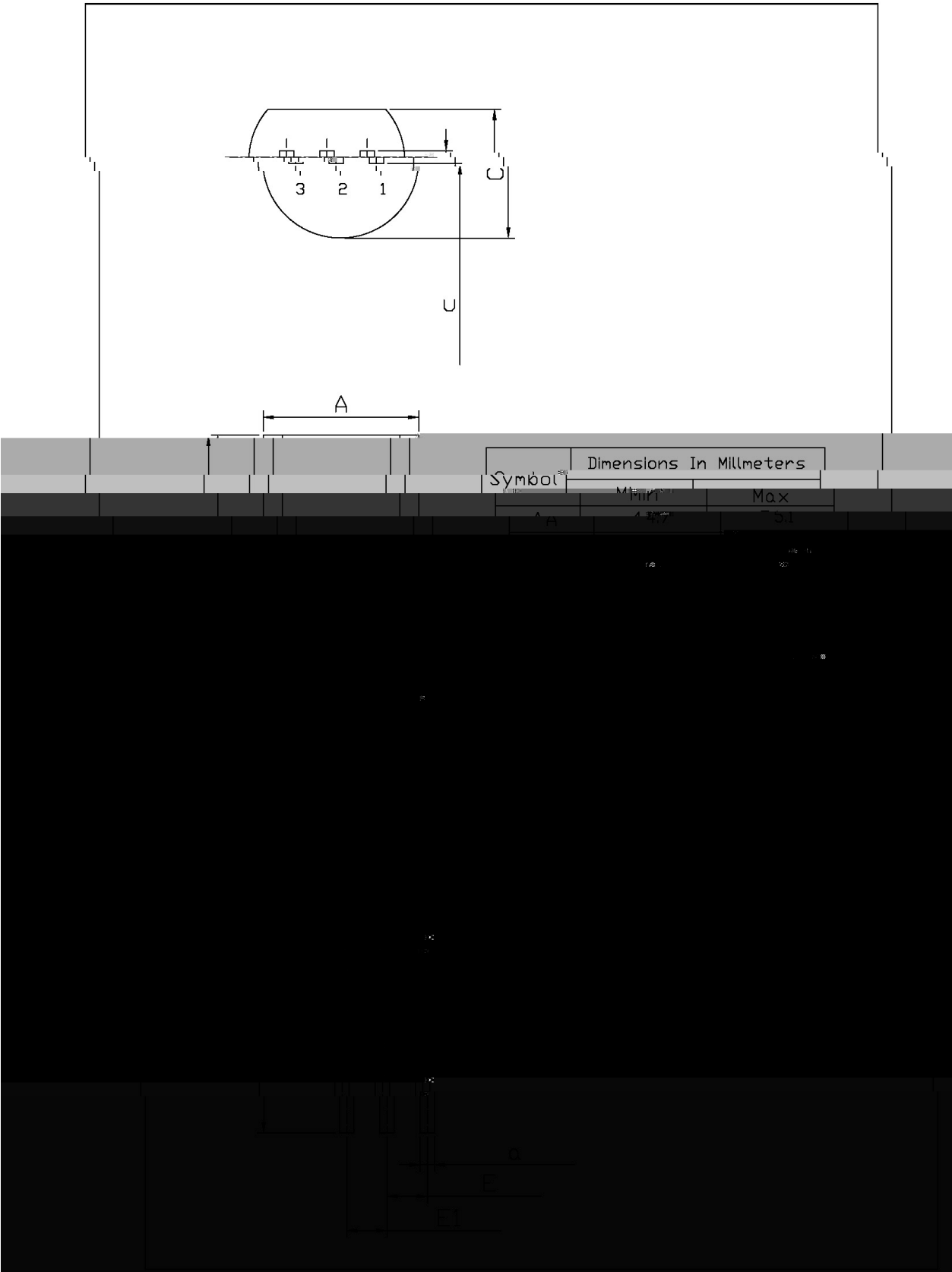
/ Electrical Characteristic Curve



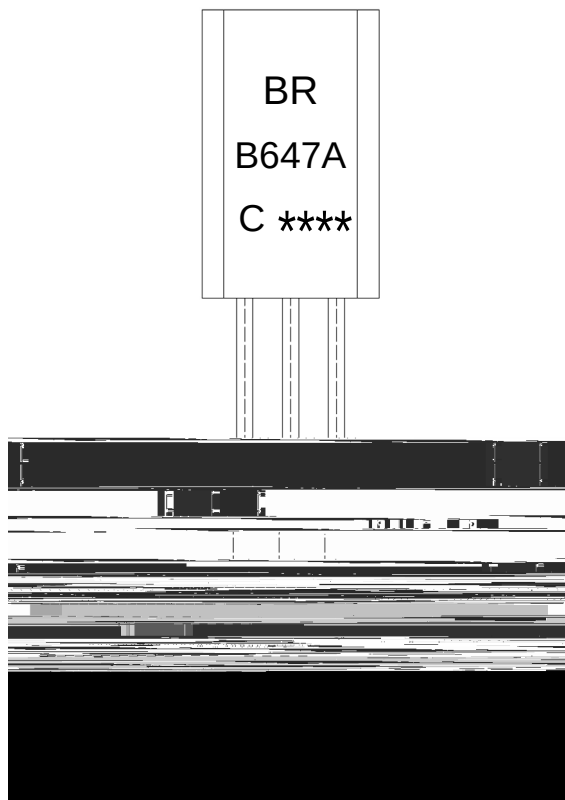
/ Package Dimensions

TO-92LM

Unit: mm



/ Marking Instructions



б " X

EU: ㄠ 3^N Γᄡ

E97:D X ㄠ 3^N Γᄡ

F: ㄠ k_{IH}⁶ Γᄡ

---- X ㄠ 1 F ᄡ^N Γᄡ 1 ㄠ 1 F ᄡ^N Ψ ᄡ

Note:

BR: Company Code.

B647A: Product Type.

C: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.

Note:
1.Preheating:25~150 ℃ , Time:60~6Tc2 18 re7.Tf1.6f150est